

EECS 141: SPRING 01 --MIDTERM 2

Prof. Andrei Vladimirescu

The transistors in the following problems are minimum-length (0.25 μm) devices fabricated in a 0.25 μm process; the only model parameters you need are the zero-bias V_{to} and back-gate bias modified V_t threshold voltages:
 NMOS: $V_{tn0} = 0.4$ V, $V_{tn} = 0.7$ V;
 PMOS: $V_{tp0} = -0.4$ V, $V_{tp} = -0.7$ V.
 The supply voltage is $V_{dd} = 2.5$ V.

Problem 1. Static CMOS Logic

Consider the two complementary static CMOS gates shown below.

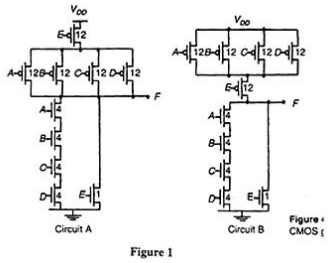


Figure 1

a) Do they implement the same logic function? What logic function(s) do they implement?

Yes No

F1 = F2 =

b) Considering the transistor sizes shown what is the worst-case input pattern (A-E) from a delay perspective for Circuit A, and, for Circuit B? Explain. Assume that an NMOS transistor has the same ON-resistance as a three times wider PMOS.

Circuit A

A= B= C= D= E=

Circuit B

A= B= C= D= E=

c) What are the worst-case propagation delays T_{pHL} and T_{pLH} ? For which Circuit, A or B, and which input patterns do they correspond? Consider $R_{eqn} = 40k$, $R_{eqp} = 120k$, $C_{dbn} = C_{dbp} = C_{sbn} = C_{sbp} = 1fF$ for a unit transistor ($W=L$) and neglect the gate-overlap capacitance. Hint: draw in each case the equivalent RC network.

$T_{pLH} =$ Ckt ABCDE= $T_{pHL} =$ Ckt ABCDE=

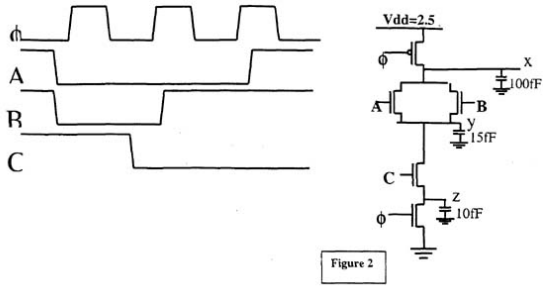
d) Consider that the inputs change in the following order: A, B, C, D, E. Which circuit performs better and why?

Ckt A Ckt B

e) Give a more appropriate sizing of the transistors (in integer multiples) of Circuit A and B which improves the propagation delay.

PROBLEM 2: Dynamic Logic

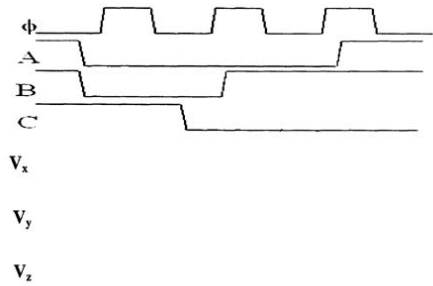
For the dynamic CMOS gate shown in Fig. 2 and considering the waveforms specified (0-2.5V).



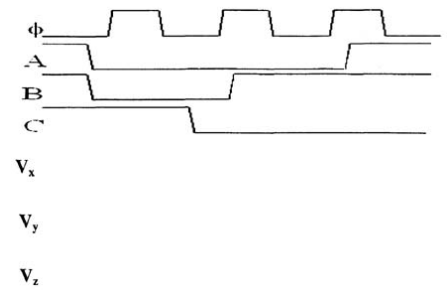
a) What is the logic function?

$F_x =$

b) Sketch the waveforms considering just the diffusion capacitances at nodes x, y, z; indicate the voltage levels for each waveform paying attention to back-gate bias when necessary.



c) Now consider that $C_{gdo} = 10\text{fF}$ of the clocking transistors cannot be neglected; draw the waveforms in this situation. You can neglect C_{gdo} for all other transistors.



d) For each of the three clock periods shown estimate the delta V on the rising (1+, 2+, 3+) and the falling edge (1-, 2-, 3-) at x and z taking into account C_{gd0} of the clocking transistors.

ϕ	1+	1-	2+	2-	3+	3-
ΔV_x						
ΔV_z						

e) Is there an upper limit for $|\Delta V|$? Explain.

$|\Delta V| =$

f) What is the average power dissipation of this circuit if it is clocked at $f=500\text{MHz}$? Consider the switching probability. Assume all inputs have equal probability of 0 or 1.

$P_{av} =$

Problem 3. Pass transistor logic.

A CPL implementation of a circuit for a very common arithmetic block is shown in Figure 3.

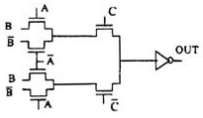


Figure 3

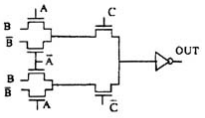
a) What is the logic function implemented and for what arithmetic block can it be used?

$F_{\text{OUT}} =$

b) All input signals are 0-2.5V and $V_{\text{dd}} = 2.5\text{V}$; show the voltage levels for a logic "0" and "1" at nodes x, y, and OUT;

Input	V _x	V _y	V _{out}
Logic 0			
Logic 1			

c) Suggest a circuit change to improve the noise margins of this circuit; draw your solution on the circuit diagram below.



d) Draw a pass-transistor circuit implementation of this function using both N- and PMOS transistors; does the solution in c) above apply to this new implementation?

e) Which solution, c) or d) is preferable and why?

Posted by HKN (Electrical Engineering and Computer Science Honor Society)
 University of California at Berkeley
 If you have any questions about these online exams
 please contact <mailto:examfile@hkn.eecs.berkeley.edu>